



Features

- Low on resistance 8 ohms
- Breakdown voltage 350V minimum
- High input impedance
- Low input and output leakage
- Small package size SOT-223
- PC Card (PCMCIA) Compatible
- PCB Space and Cost Savings

Applications

- Support Component for LITELINK™ Data Access Arrangement (DAA)
- Telecom

Description

The CPC5602C is an “N” channel depletion mode Field Effect Transistor (FET) that utilizes Clare’s proprietary third generation vertical DMOS process. The third generation process realizes world class, high voltage MOSFET performance in an economical silicon gate process. The vertical DMOS process yields a highly reliable device particularly in difficult application environments such as telecommunications.

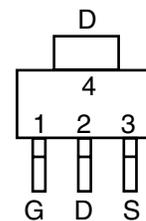
One of the primary applications for the CPC5602C is as a linear regulator/ hook switch for the LITELINK™ family of Data Access Arrangements (DAA) Devices CPC5610A, CPC5611A, CPC5620 and CPC5621A.

The CPC5602C has a typical on-resistance of 8Ω, a breakdown voltage exceeding 350V and is available in an SOT-223 package. As with all MOS devices, the FET structure prevents thermal runaway and thermal-induced secondary breakdown.

Ordering Information

Part #	Description
CPC5602C	N- Channel Depletion Mode FET, SOT-223 Package
CPC5602CTR	N- Channel Depletion Mode FET, SOT-223 Package Tape and Reel (1000 units min)

Package Pinout



Pin #	Name
1	GATE
2	DRAIN
3	SOURCE
4	DRAIN

Absolute Maximum Ratings (@ 25° C)

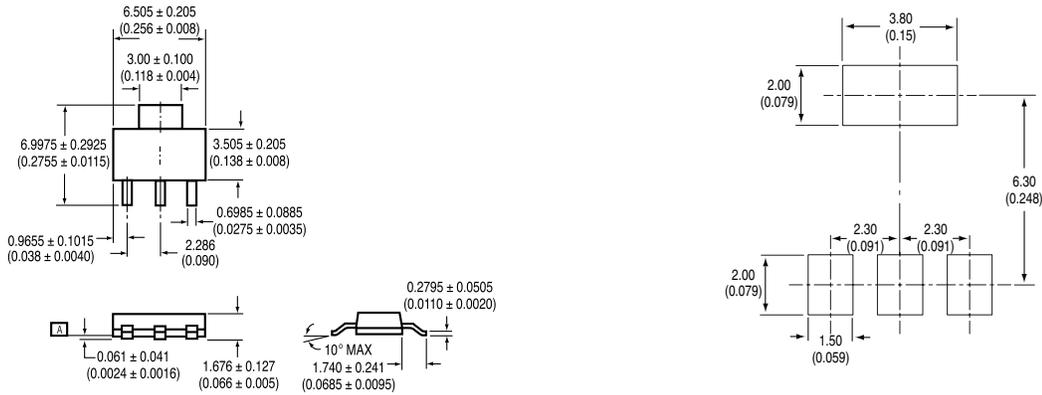
Parameter	Min	Max	Units
V _{DS} Voltage	-	350	V
Total Package Dissipation	-	2.5	W
Operational Temperature	-40	+85	°C
Storage Temperature	-40	+125	°C
Soldering Temperature (10 seconds Max)	-	+220	°C

Absolute Maximum Ratings are stress ratings. Stresses in excess of these ratings can cause permanent damage to the device. Functional operation of the device at conditions beyond those indicated in the operational sections of this data sheet is not implied.

Electrical Characteristics (@25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Breakdown Voltage	V _{(BR)DS}	-	350	-	-	V
Gate-to-Source Off Voltage	V _{GS(off)}	I _D = 2μA, V _{DS} =10V, V _{DS} =100V	-3.9	-	-2	V
Drain-to-Source Leakage Current	I _{DS(off)}	V _{GS} = -5V, V _{DS} =110V	-	-	1	μA
		V _{GS} = -5V, V _{DS} =350V	-	-	100	μA
Drain Current	I _D	V _{GS} = -2.7V, V _{DS} =5V, V _{DS} =50V	-	-	5	mA
		V _{GS} = -0.57V, V _{DS} =5V	130	-	-	mA
On Resistance	R _{DS(on)}	V _{GS} = -0.35V, I _{DS} =50mA	-	8	14	Ω
Gate Leakage Current	I _{GSS}	V _{GS} =10V, V _{GS} =-10V	-	-	0.1	μA
Gate Capacitance	C _{ISS}	V _{DS} = V _{GS} =0V	-	-	300	pF
Thermal Resistance	θ _{JC}	-	-	-	14	°C/W

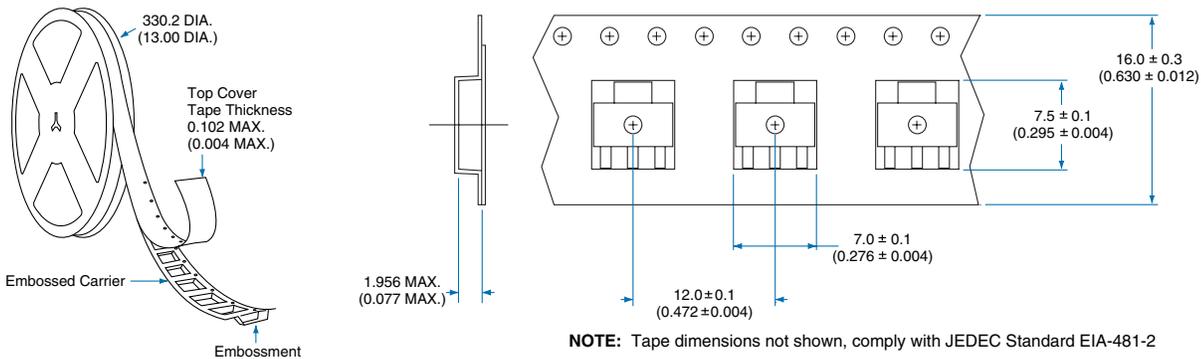
MECHANICAL DIMENSIONS



Coplaner to **A** 0.08/(0.003) 4 PL.

Note: Values are typical except where noted.

Tape and Reel Packaging for the SOT-223



DIMENSIONS:
mm
(inches)

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